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|--|----------|----|----|
| Peak gate power | P_{GM} | 10 | W |
| Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.7) | V_{pp} | 4 | kV |

ELECTRICAL CHARACTERISTICS ($T_j=25$ unless otherwise specified)

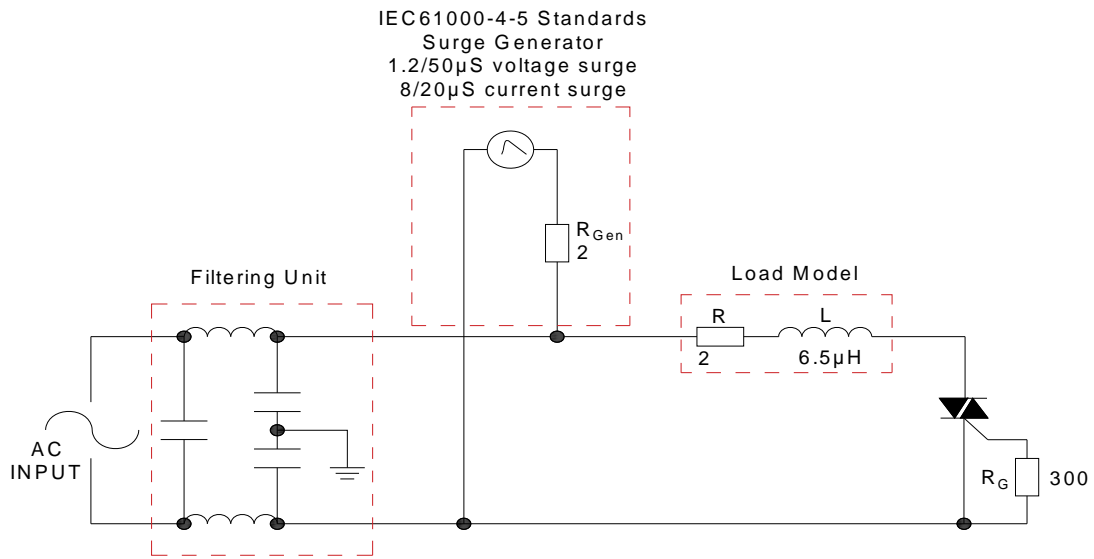
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|----------|-------------------------------------|-----|------|-----|----|
| | | | | | |
| I_{GT} | $V_D=12V R_L=33$ | - - | MAX. | 35 | mA |
| V_{GT} | | - - | MAX. | 1 | V |
| V_{GD} | $V_D=V_{DRM} T_j=125$ $R_L=3.3k$ | - - | MIN. | 0.2 | V |
| | | - | | 50 | |
| I_L | $I_G=1.2I_{GT}$ | | MAX. | 60 | mA |
| | | | | | |
| I_H | $I_T=500mA$ | | MAX. | 40 | mA |
| dV/dt | $V_D=400V$ Gate Open T_j | | | | |



ORDERING INFORMATION



FIG.7 ÖTest circuit for inductive and resistive loads to IEC-61000-4-5 standards



LEAD FORMING AND SOLDERING

Refer to the application note "Assembly Instructions for Thyristors in Through-hole Package" released by JieJie
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PACKAGE MECHANICAL DATA

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